

Magnetism and Electron Transport in nano structures

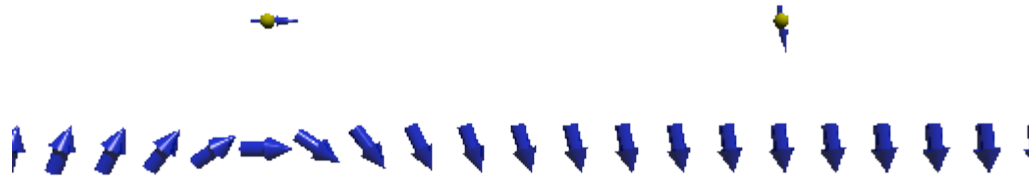


Figure courtesy of
Dr. J. Ohe

多々良源

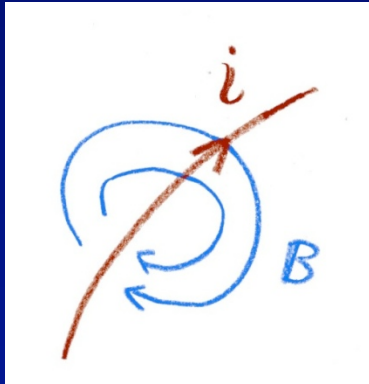
Gen Tatara

首都大学東京 大学院理工学研究科

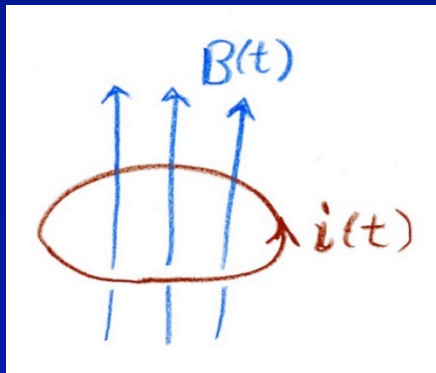
Tokyo Metropolitan Univ. and PRESTO JST

Hiroshi Kohno(Osaka), Junya Shibata(Kanagawa)
Junichiro Ohe(Hamburg), Akihito Takeuchi (TMU)

Magnetism and electric current



Current \Rightarrow Magnetic field
Ampere (~1820)

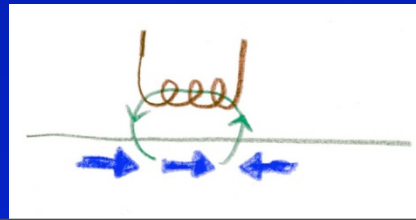


Magnetic field \Rightarrow Current
Faraday (~1830)



Ampere law:

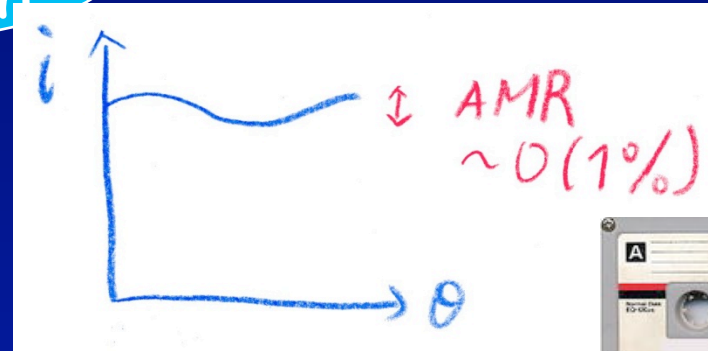
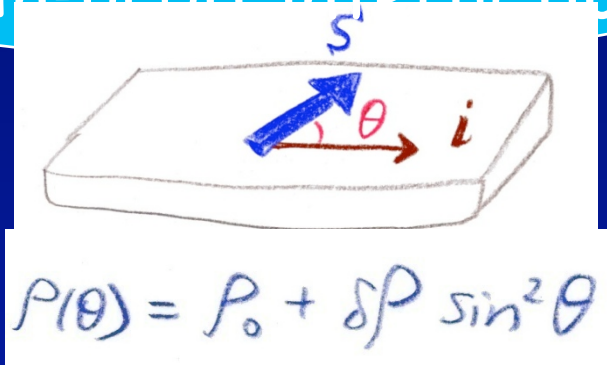
write in mechanism of all magnetic devices



Beyond Maxwell equation

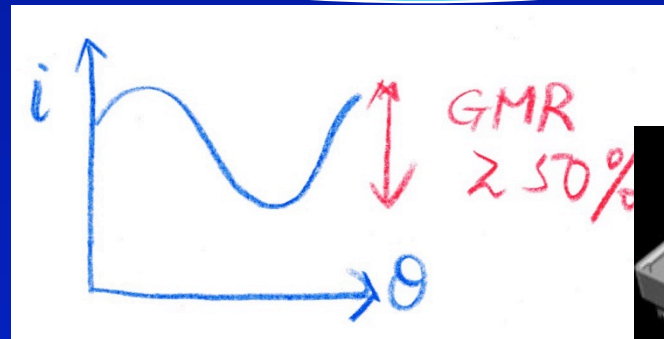
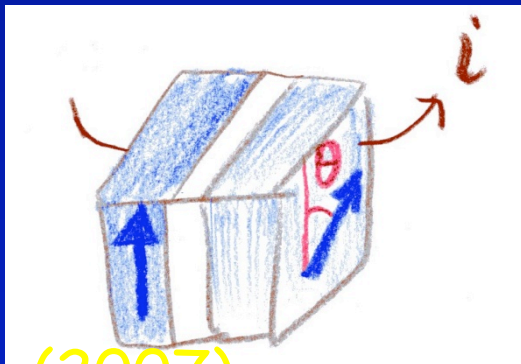
- Read out mechanism (20 cent.)

- Spin-orbit interaction



AMR : Anisotropic MagnetoResistance

- Nanostructure and exchange interaction



Nobel prize (2007)

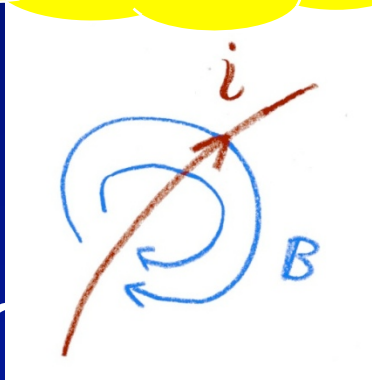
GMR : Giant MR (1988), Tunnel MR

19 cent.

20 cent.~

Maxwell equation

current
↓
magnetism



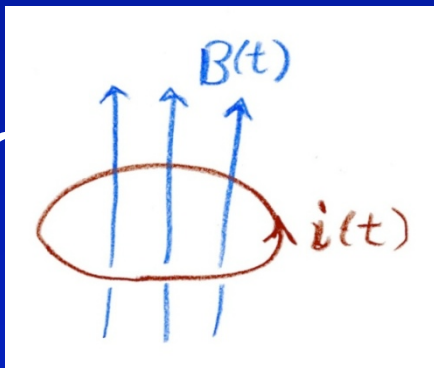
Ampere

Material
and structure

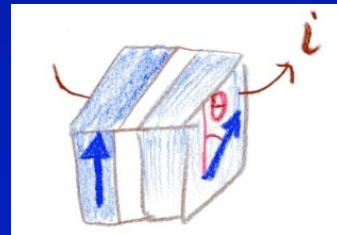
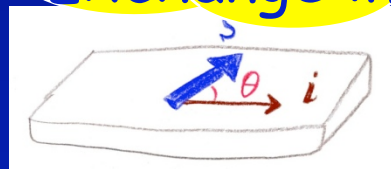
Spin-orbit

Exchange interaction

magnetism
↓
current



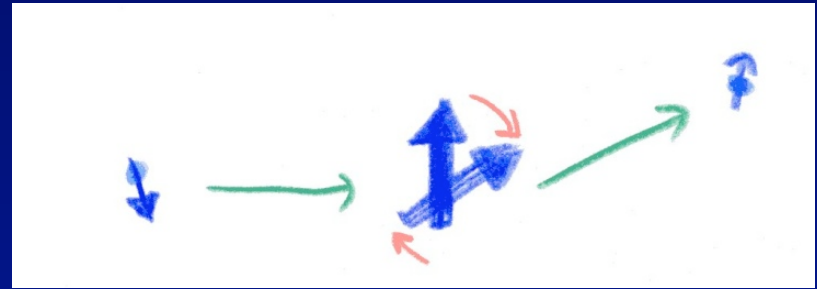
Faraday



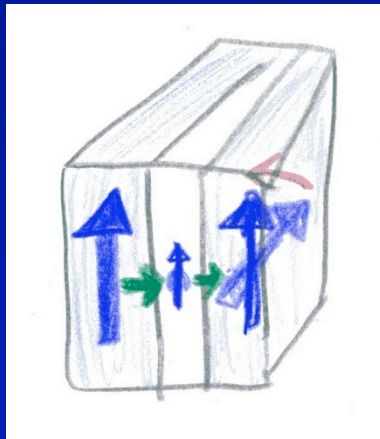
AMR, GMR('88),
TMR

•sd Exchange interaction

$$J \int dx \vec{S}(x) \times c^+ \vec{\sigma} c(x)$$



Transfer of spin between local spin and conduction electron



Magnetization flip by spin polarized current

Slonczewski, Berger '96

Spin transfer effect

Without magnetic field

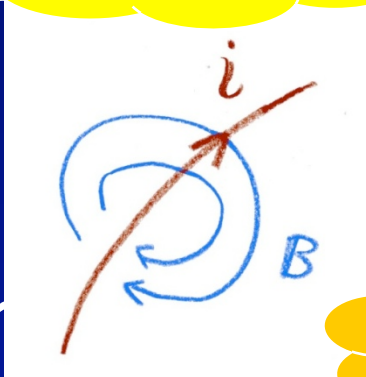
19 cent.

20 cent.~

21 cent.~(??)

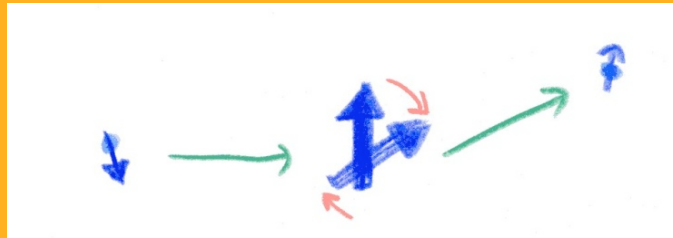
Maxwell equation

current
↓
magnetism



Ampere

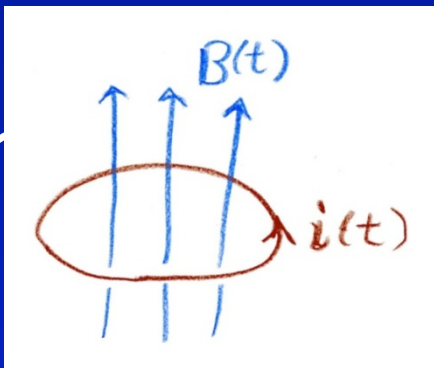
Material
and structure
Spin-orbit
Exchange interaction



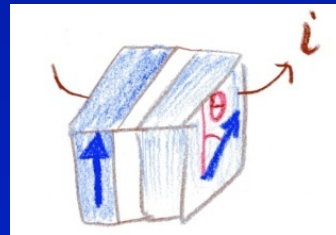
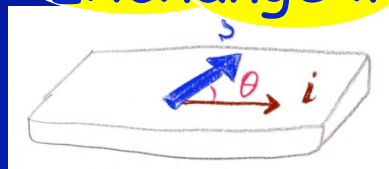
Spin transfer
Berger, Slonczewski
1978-, '96

Efficient in
Nano scale

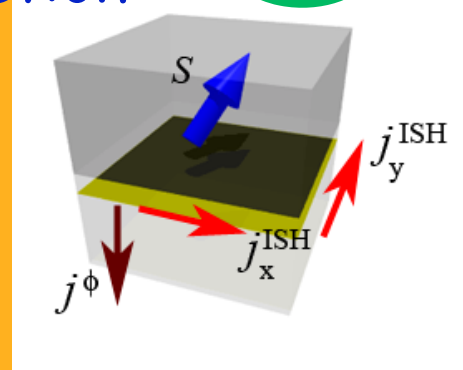
magnetism
↓
current



Faraday



AMR, GMR('88),
TMR



Inverse spin Hall
Saitoh, Miyajima'06

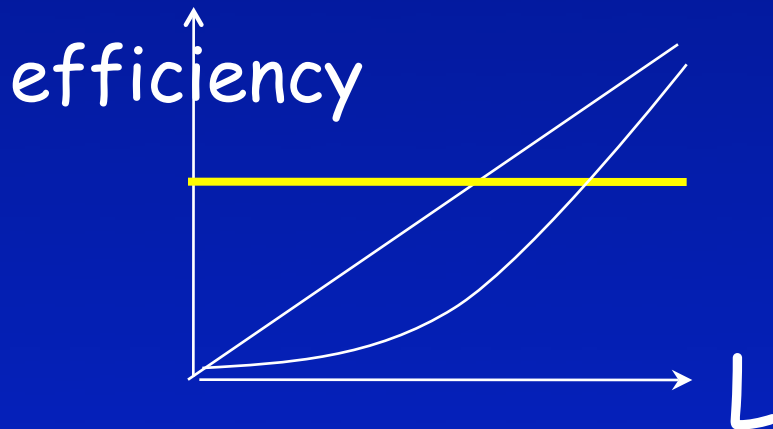
Why useful ?

- Effects survives in nano scale

↔ Ampere,

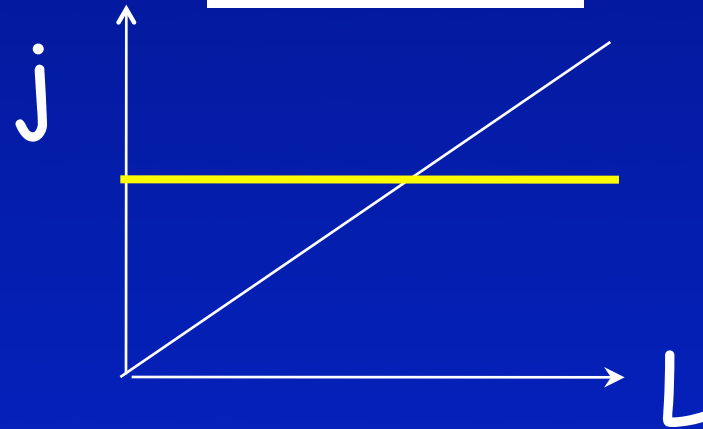
- Ampere field ^{Faraday}

$$B \propto I \propto L^2 j$$



- Faraday

$$j \propto \frac{S}{L} \dot{M} \propto L$$



- Spin transfer and inverse spin Hall: remains finite for $L \rightarrow 0$

PART 1 :

Current-driven magnetization switching

- behavior of domain wall under current

- Does it moves by current?
- What is the threshold current?
- How fast?



Model sd model of ferromagnets Rigid wall : $K \gg K_{\perp}$

- Magnetization (local spin)
- Conduction electron
- + Exchange

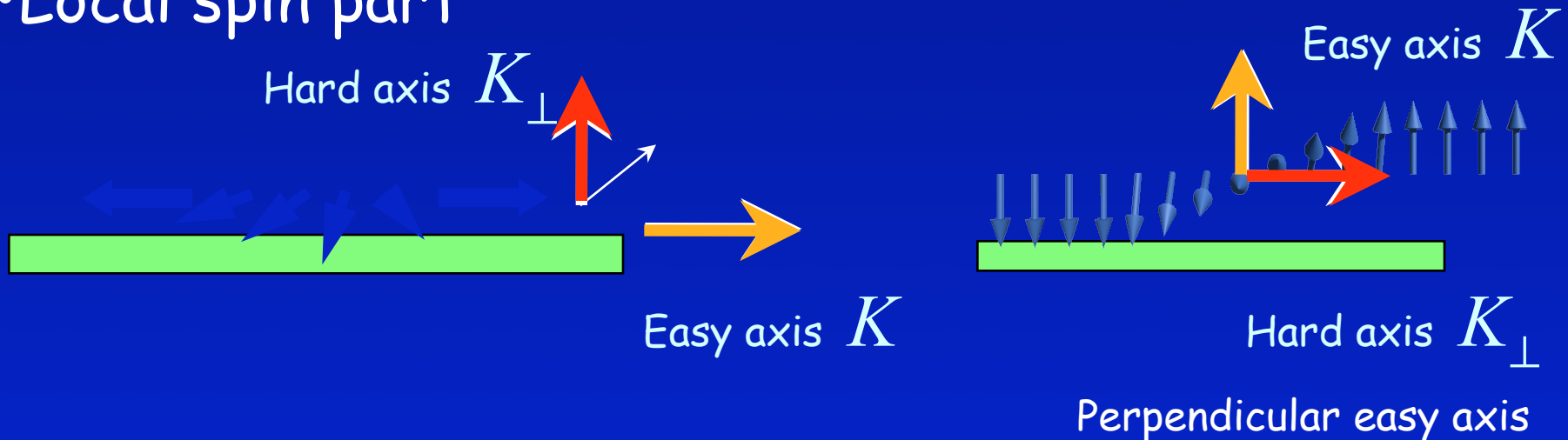
Out of plane
Energy
(dynamics)

Rigidity of DW

$$L = \int dx \left(-\hbar S \dot{\phi} (1 - \cos \theta) - \frac{1}{2} \left(J (\nabla S)^2 - K S_z^2 - K_{\perp} S_y^2 \right) \right)$$

$$+ \sum_k c_k^{\dagger} (i\hbar \partial_t - \varepsilon_k) c_k + H_{sf} + \Delta \int dx \vec{S}(x) \times c^{\dagger} \vec{\sigma} c(x)$$

• Local spin part

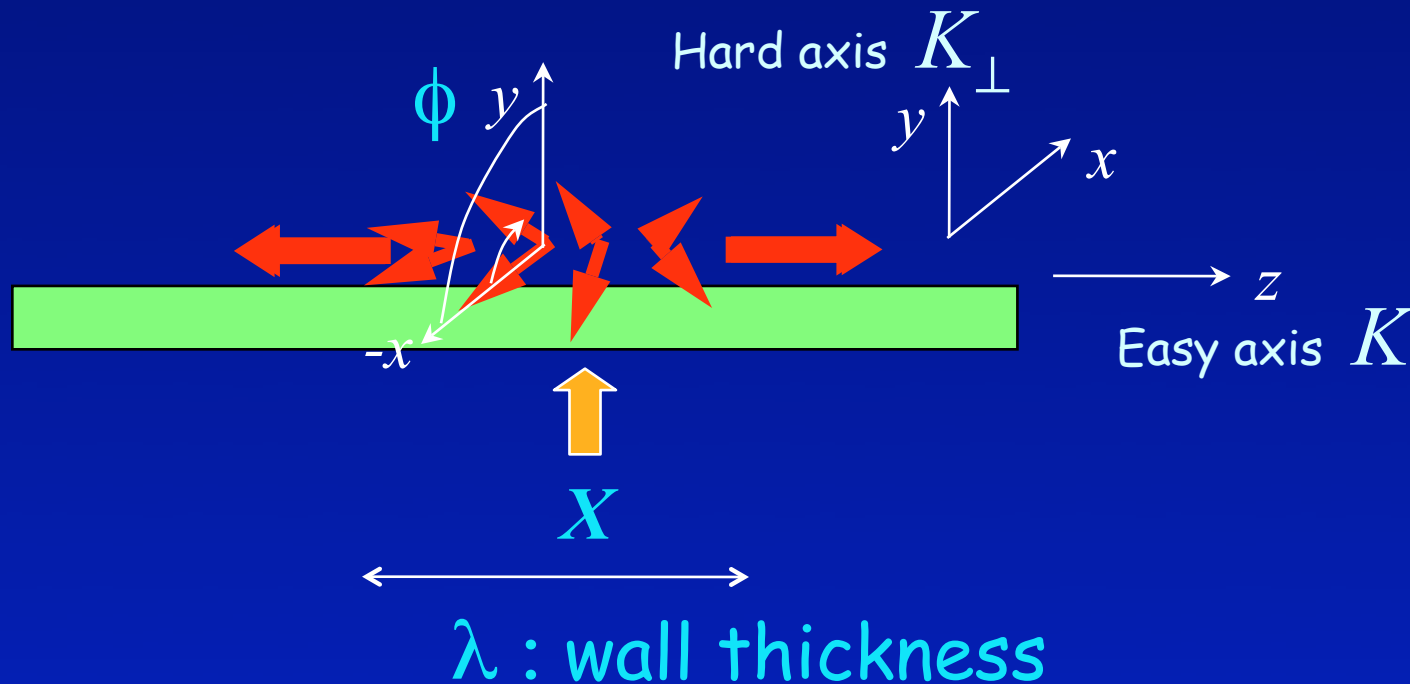


Description of DW

- Rigid 1D wall $K \gg K_{\perp}$

Low energy dynamics of DW is described by X and ϕ

Slonczewski ('72)
Berger ('78-93)
Braun & Loss ('96)
Takagi & GT ('96)



Other deformations are high-energy mode

Model sd model of ferromagnets

- Magnetization (local spin)
- Conduction electron
- + Exchange interaction

Close to adiabatic limit

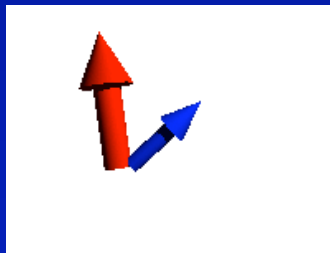
$$\frac{v_F}{\lambda} \frac{\hbar}{\Delta} \ll 1$$

$$L = \int dx \left(-\hbar S \dot{\phi} (1 - \cos \theta) - \frac{1}{2} \left(J (\nabla S)^2 - K S_z^2 + K_{\perp} S_y^2 \right) \right)$$

$$+ \sum_k c_k^{\dagger} (i\hbar \partial_t - \varepsilon_k) c_k + H_s + \Delta \int dx \vec{S}(x) \times c^{\dagger} \vec{\sigma} c(x)$$

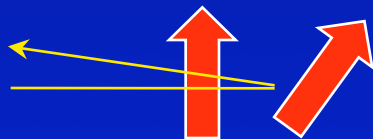
• Exchange interaction

• torque



$$\tau = \int dx \vec{S}(x) \times \vec{s}(x) \quad \text{Berger '92}$$

• force



$$F = \int dx \nabla \vec{S}(x) \times \vec{s}(x) \quad \text{Berger '84}$$

• Equation of motion of DW under current

$\frac{\delta}{\delta X}$

$$\frac{\hbar SN}{\lambda} \left(\dot{\phi} + \alpha \frac{\dot{X}}{\lambda} \right) = -\Delta \int d^3x \nabla \vec{S} \times \vec{\sigma}$$

Force

$\frac{\delta}{\delta \phi}$

$$\frac{\hbar SN}{\lambda} \left(\dot{X} - \alpha \lambda \dot{\phi} \right) = -\frac{NS^2 K_{\perp}}{2} \sin 2\phi - \Delta \int d^3x (\vec{S} \times \vec{\sigma})$$

Torque

Coupled non-linear equation of X and ϕ

σ : electron spin density in the presence of DW

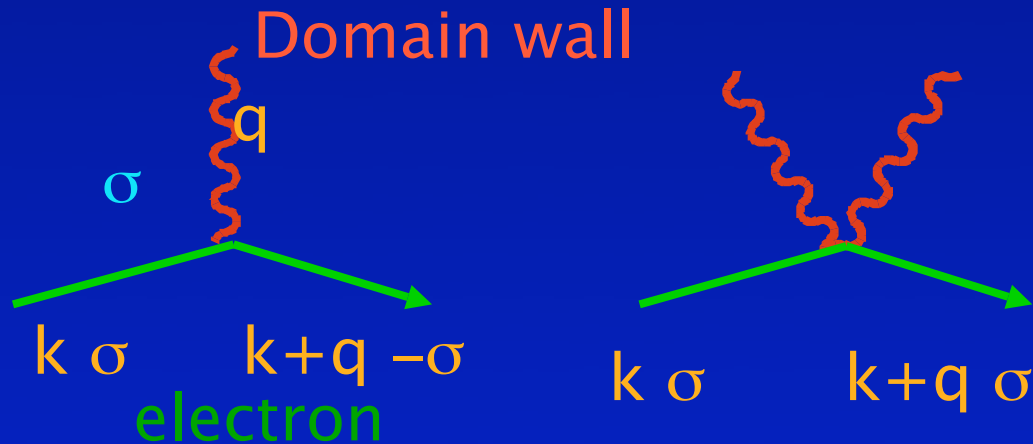
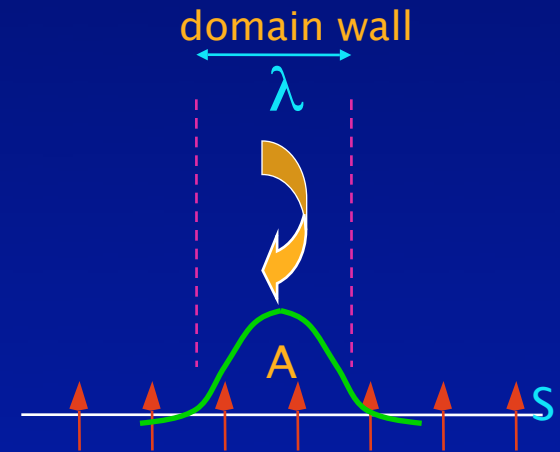
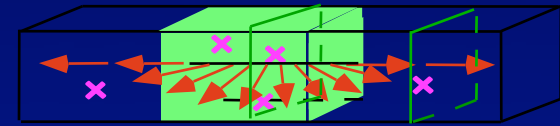
effect of electric current

α : Gilbert damping (friction)

Domain wall

- Described by $SU(2)$ gauge field

$$\partial_{\mu} \vec{S} = (\vec{A}_{\mu} \times \vec{S})$$



• Force and torque due to electron

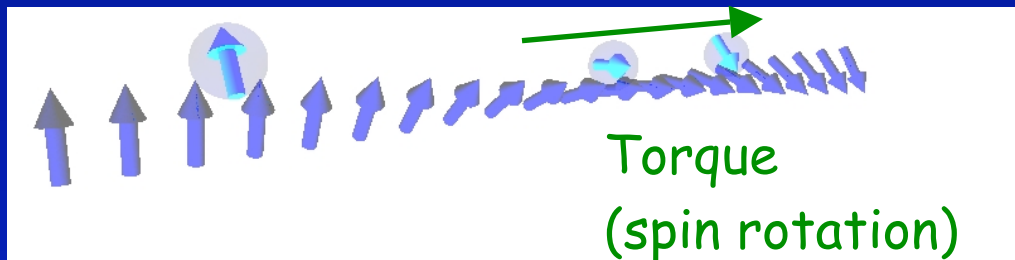
$$\frac{\hbar SN}{\lambda} \left(\dot{\phi} + \alpha \frac{\dot{X}}{\lambda} \right) = -\Delta \int d^3x \nabla \vec{S} \times \vec{\sigma}$$

$$\frac{\hbar SN}{\lambda} (\dot{X} - \alpha \lambda \dot{\phi}) = -\frac{NS^2 K_{\perp}}{2} \sin 2\phi - \Delta \int d^3x (\vec{S} \times \vec{\sigma})$$

Under electron flow \rightarrow Keldish Green function (electron) $G^<$

• Torque $\int d^3x \mathbf{S} \times \boldsymbol{\sigma} = \mathbf{S} \times \text{[circle]}$ $\xrightarrow{\text{thick wall}}$ $\propto j_s$

domain wall



Spin current

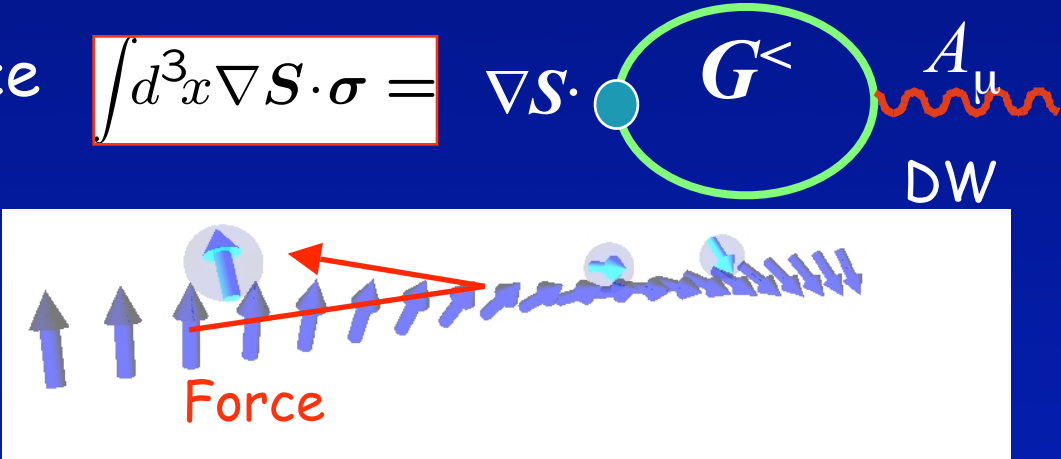
• Non-adiabatic correction (finite DW width)

$$\frac{\hbar SN}{\lambda} \left(\dot{\phi} + \alpha \frac{\dot{X}}{\lambda} \right) = -\Delta \int d^3x \nabla \vec{S} \times \vec{\sigma}$$

$$\frac{\hbar SN}{\lambda} (\dot{X} - \alpha \lambda \dot{\phi}) = -\frac{NS^2 K_{\perp}}{2} \sin 2\phi - \Delta \int d^3x (\vec{S} \times \vec{\sigma})$$

• force $\int d^3x \nabla S \cdot \sigma = \nabla S \cdot \textcircled{G^<} \overset{A_{\mu}}{\sim} \text{DW} = \boxed{eN\rho_w j}$

ρ_w : DW resistivity
 Dominates for thin wall

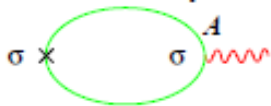


Electron spin density and torques: results

$$\vec{J}_S \times \vec{n} \quad n: \text{local spin}$$

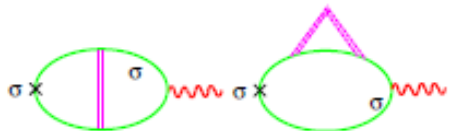
- Local torque

Torque from electron



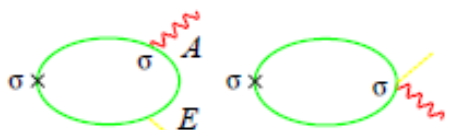
$$\tau \propto \dot{n}$$

spin renormalization



$$\frac{1}{\tau_{sf}} n \times \dot{n}$$

Gilbert damping α



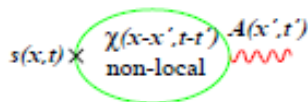
$$(j_s \cdot \nabla) n$$

Spin transfer torque



$$\frac{1}{\tau_{sf}} [n \times (j \cdot \nabla) n]$$

β -term



$$\tau_{nl}$$

momentum transfer force

$$\alpha_{sf} \dot{\vec{S}} + P j \times \nabla \vec{S} + \beta_{sf} (\vec{S} \times j \times \nabla \vec{S}) + \dots$$

P: spin polarization

Domain wall dynamics under current

- ▶ Equation of motion of transverse wall

$$\dot{X} - \alpha \lambda \dot{\phi}_0 = \frac{K_{\perp} \lambda}{2\hbar} S \sin 2\phi_0 + \frac{a^3}{2S} P \frac{j}{e}$$

$$\dot{\phi}_0 + \alpha \frac{\dot{X}}{\lambda} = \beta j + f_{\text{pin}}$$

Berger '84

GT & Kohno '04

- ▶ $\beta = \left(\frac{ena^3}{2\hbar S} R_w A + P \beta_{\text{sf}} \right)$

λ : domain wall thickness

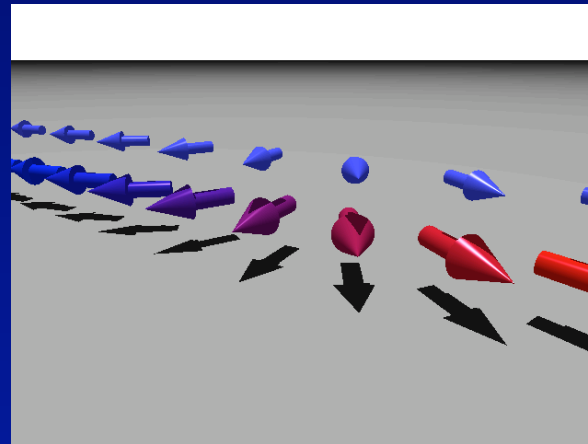
Non-adiabaticity

spin relaxation, reflection

Domain wall dynamics under current

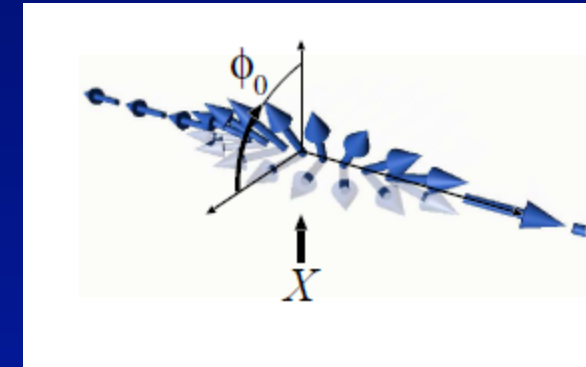
Spin polarization of conduction electron

Adiabatic component

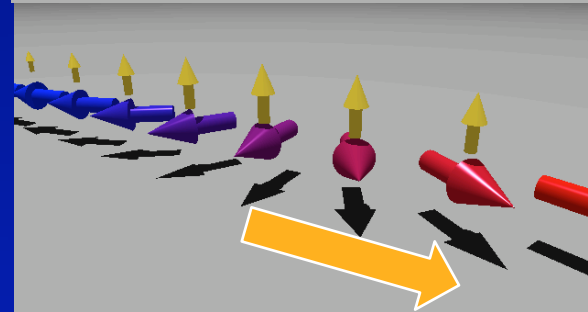


σ

S



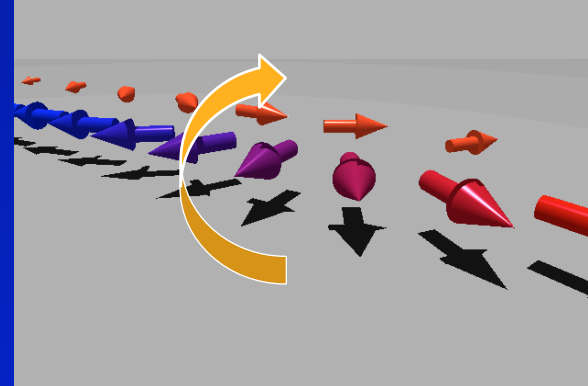
Spin transfer



Translation

$$\dot{X} \propto j_s$$

Spin relaxation
Non-adiabaticity



Tilting

$$\dot{\phi} \propto j_s$$

Domain wall dynamics under current

- ▶ Equation of motion of transverse wall

$$\dot{X} - \alpha \lambda \dot{\phi}_0 = \frac{K_{\perp} \lambda}{2\hbar} S \sin 2\phi_0 + \frac{a^3}{2S} P \frac{j}{e}$$

$$\dot{\phi}_0 + \alpha \frac{\dot{X}}{\lambda} = \beta j + f_{\text{pin}}$$

Berger '84

GT & Kohno '04

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λ : domain wall thickness

Non-adiabaticity

spin relaxation, reflection

Domain wall dynamics under current

- ▶ Equation of motion of transverse wall

$$\dot{X} - \alpha \lambda \dot{\phi}_0 = \frac{K_{\perp} \lambda}{2\hbar} S \sin 2\phi_0 + \frac{a^3}{2S} P \frac{j}{e}$$

$$\dot{\phi}_0 + \alpha \frac{\dot{X}}{\lambda} = \beta j + f_{\text{pin}}$$

Berger '84

GT & Kohno '04

- ▶ $\beta = \left(\frac{ena^3}{2\hbar S} R_w A + P\beta_{\text{sf}} \right)$

Non-adiabaticity

Spin relaxation (spin-orbit)

λ : domain wall thickness

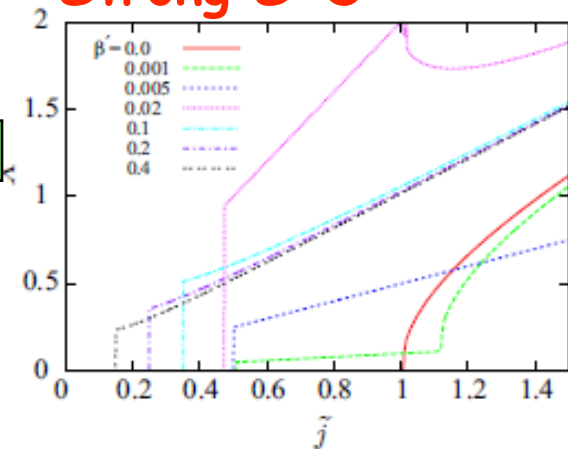
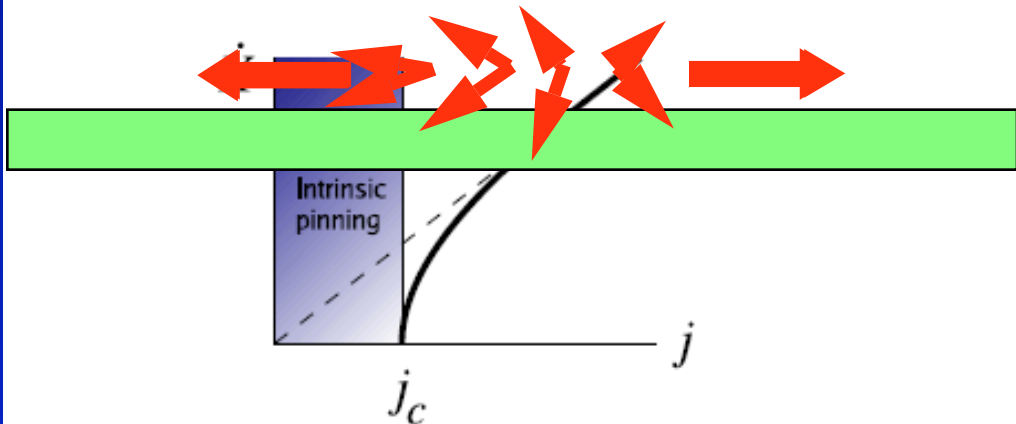
- ▶ Threshold currents

• $\beta \lesssim \alpha$ Intrinsic pinning

Thick wall

• $\beta \gtrsim \alpha$ Extrinsic pinning

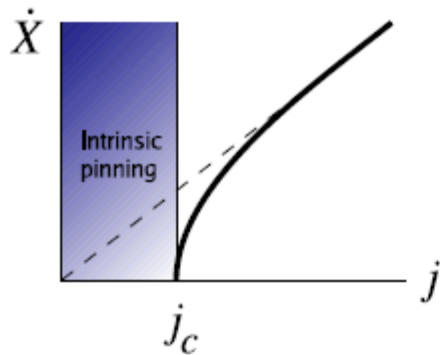
Thin wall or
Strong S-O



Domain wall dynamics under current

▶ Threshold currents

• $\beta \lesssim \alpha$ Intrinsic pinning



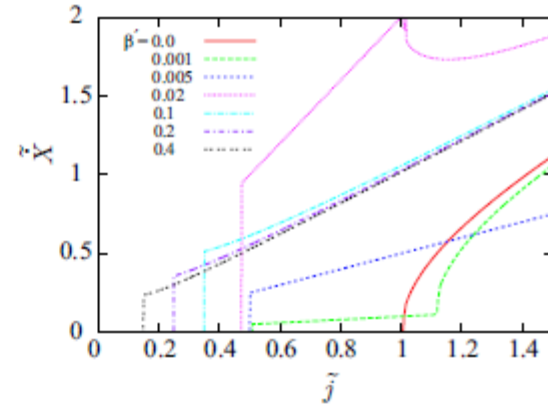
$$j_c \approx K_{\perp} \quad \text{Anisotropy energy}$$

K_{\perp} : sample geometry

$$v = P \frac{a^3}{2eS} j$$

Angular mom. conservation

• $\beta \gtrsim \alpha$ Extrinsic pinning



$$j_c \approx \sqrt{K_{\perp} V_0}$$

V_0 : extrinsic pinning

$$j_c \approx V_0 / \beta$$

V_0 : sample quality

β : wall thickness, spin-orbit

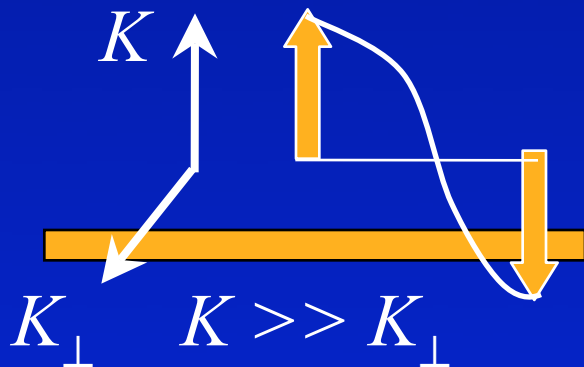
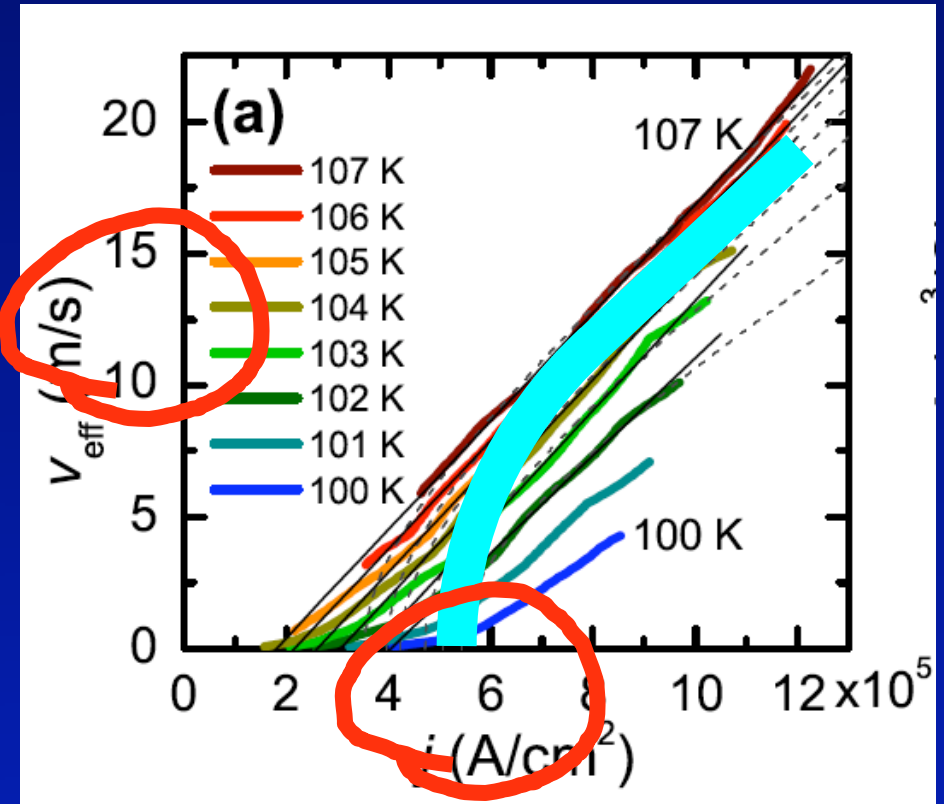
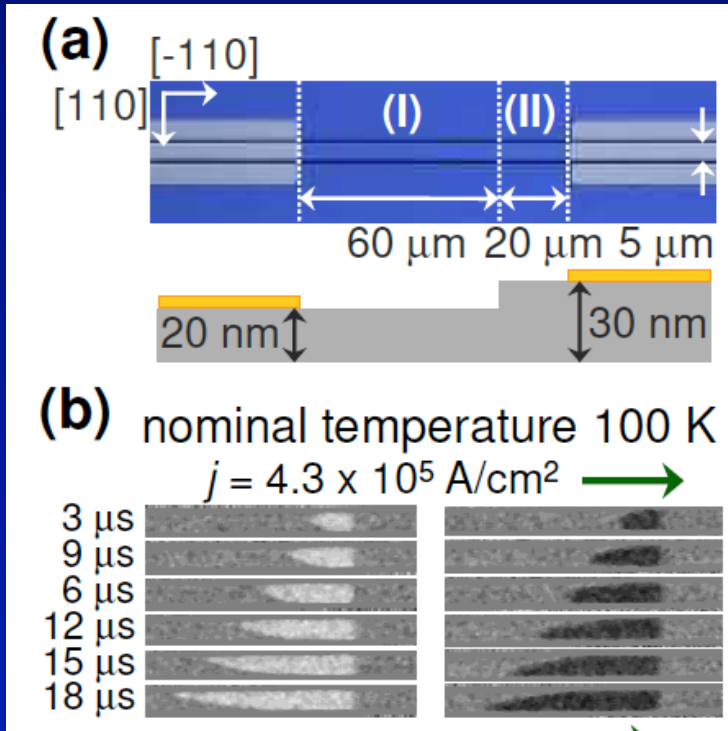
$$v = (\beta / \alpha) j \quad \text{Small } j$$

Experiment

rigid DW

GaMnAs

Yamanouchi, Chiba, Matsukura, Dietl & Ohno, PRL (2006)



Intrinsic pinning *GT & Kohno ('04)*

Spin transfer Small β

T-dependence (creep): Ieda, Maekawa

Behavior of threshold (metals)

$$j_c \propto K_{\perp} \lambda \quad \text{If intrinsic pinning}$$

• Yamaguchi, Ono

J_c depends

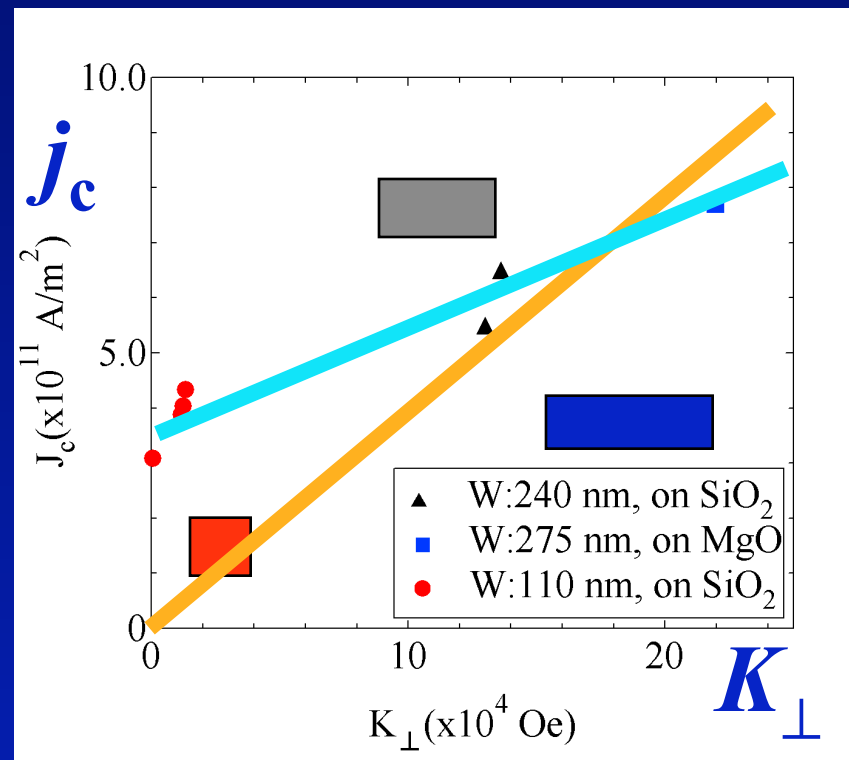
on sample geometry (K_{\perp})

(but weakly)

• Origin of threshold ?

• Deformation, creep?

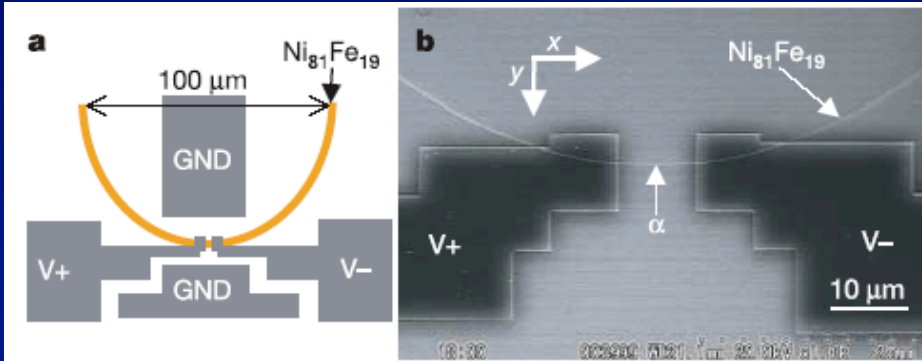
• Heating?



Manipulation by AC current

• E. Saitoh et al, Nature 432, 203 (2004)

Small current, small deformation



DW motion by use of resonance

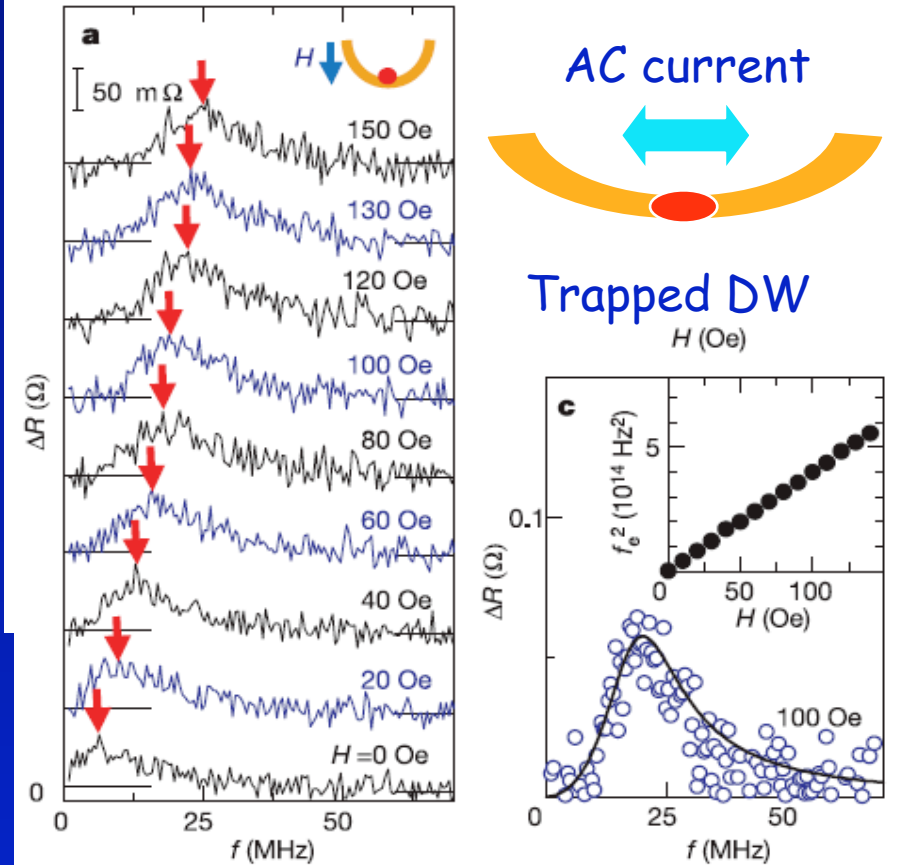
• Low-current operation

$$j \approx 10^{10} [\text{A/m}^2]$$

Resonance
at 20 MHz

• Force dominates

• Determination of DW character



$$m = 6.6 \times 10^{-23} \text{ kg}$$

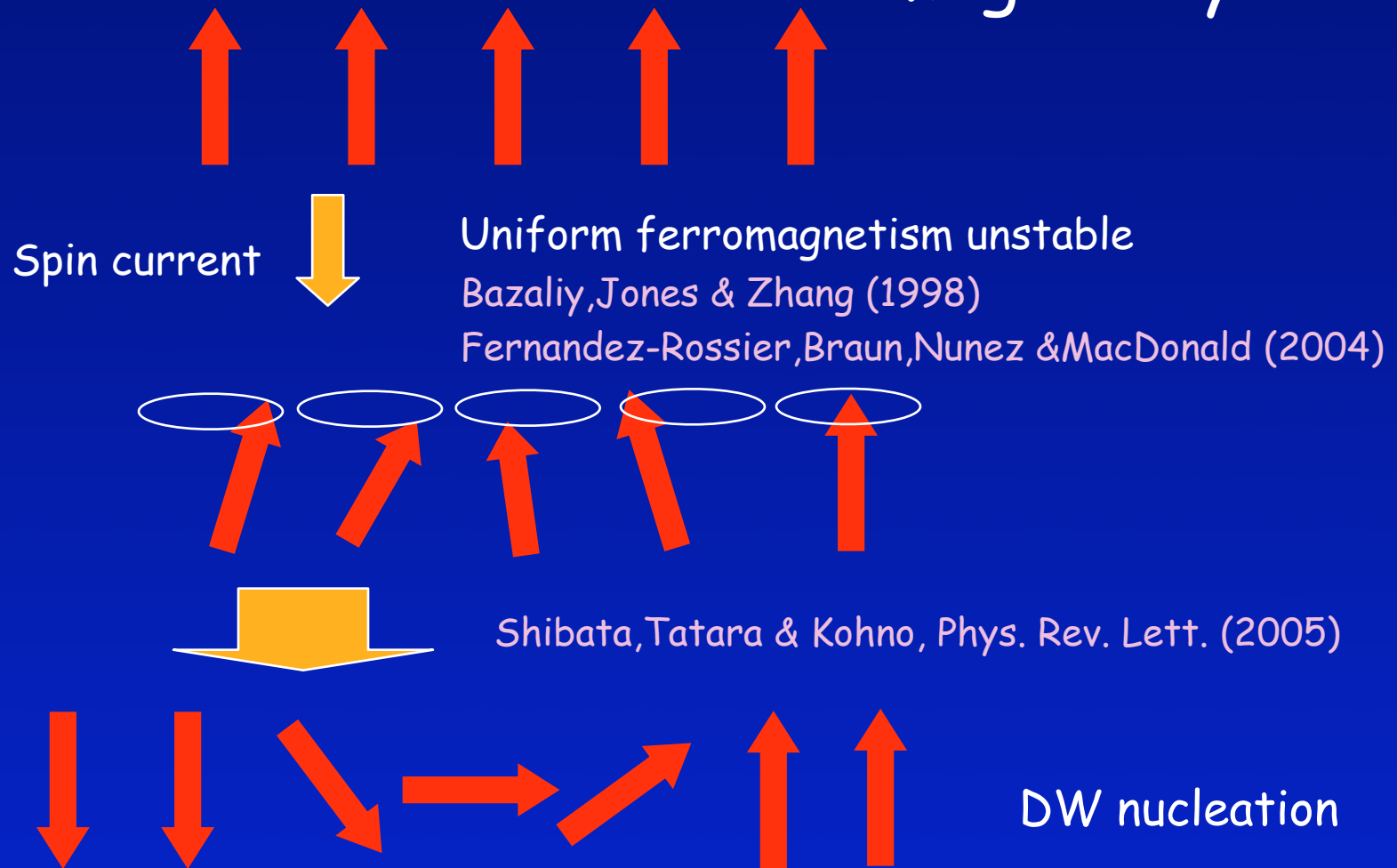
$$\tau = 10^{-8} \text{ s } (\alpha = 0.01)$$

$$R_w = 10^{-4} \Omega$$

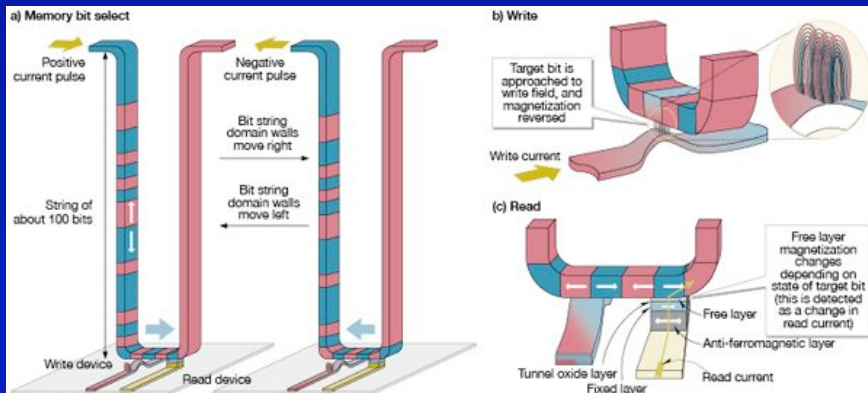
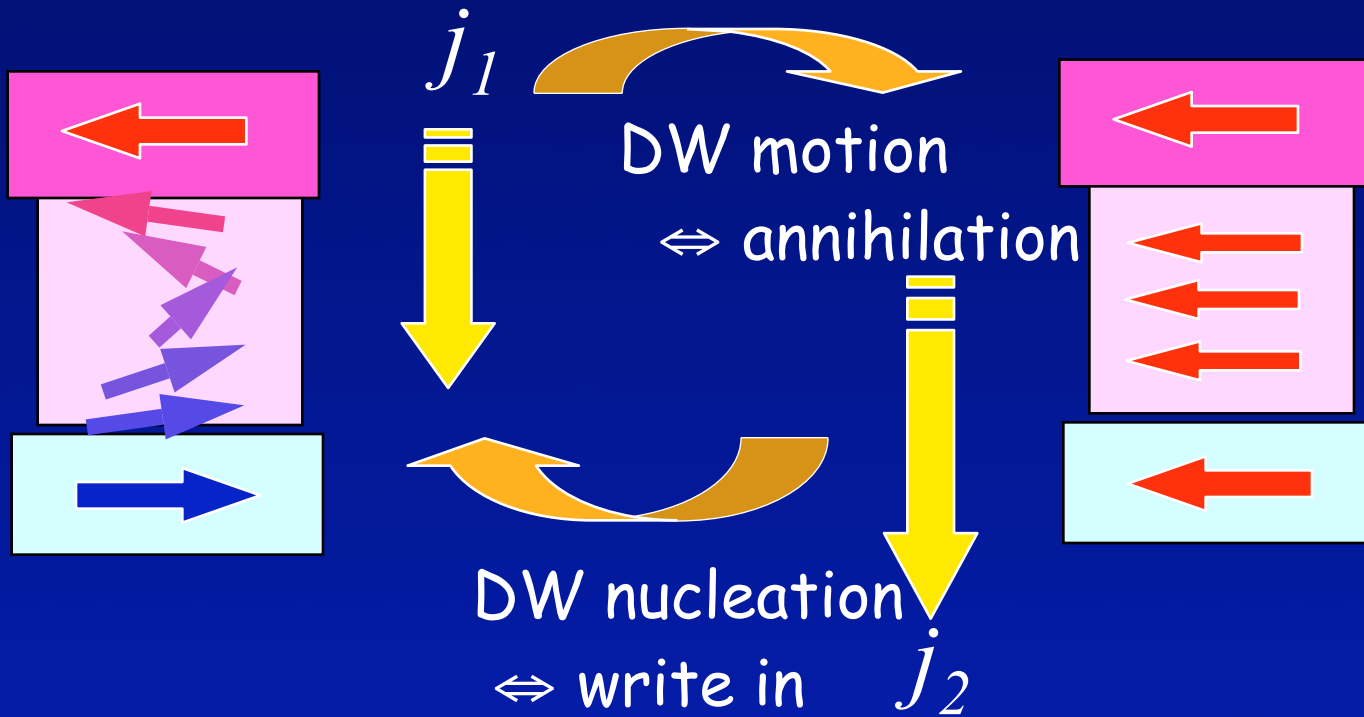
• Thomas, Parkin et al, Nature (2006)

• Domain wall nucleation by spin current

Spin current favors spin Berry phase
inhomogeneity



• DW devices operated by Current



Using Current Pulses to Move Magnetic Domain Walls Magnetic Race-Track Memory records a string of about 100 bits of information perpendicularly to the Si substrate for each read/write device. This means information density is about 100 times higher than MRAM. Operating principles are shown for access memory bit select (a), write (b) and read (c). When selecting the memory bit for access a current pulse is applied to the magnetic material, causing the magnetic domain wall to move. A positive current pulse will move the wall to the right in the diagram, and a negative one to the left. The quantity of pulses can be controlled for random access, with data read executed after the target bit has been accessed. (Diagram by Nikkei Electronics based on material courtesy IBM)

DW racetrack memory (MRAM)

S. Parkin (IBM)

Current-driven domain wall motion

- Aim

- Low current operation

- Fast motion

By factor of 10-100

$$j_c = 10^{10} \text{ A/m}^2$$

$$v = 100 \text{ m/s}$$

Theory

- Material (spin-orbit)

- Shape (anisotropy)

- Surface (reduce extrinsic pinning)

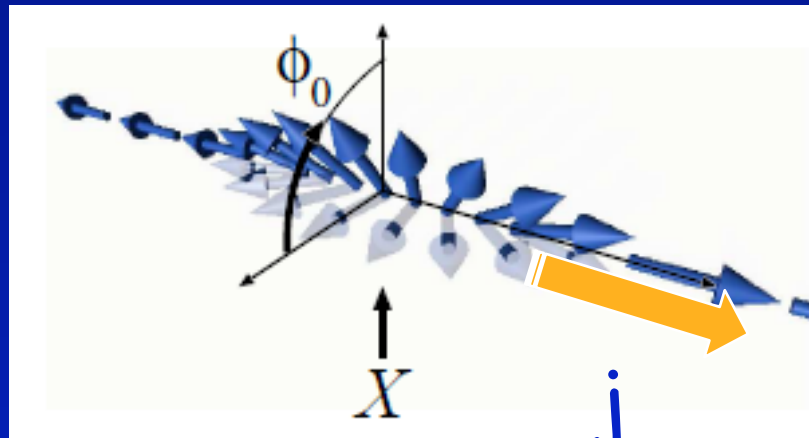
PART 2 :

Current from Magnetization dynamics

Inverse (reciprocal) spin Hall effect

Saitoh, Miyajima '06

Part 1: Current \Rightarrow Spin current \Rightarrow Magnetization dynamics



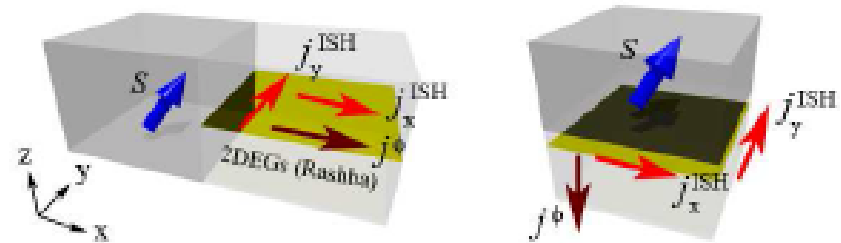
Magnetization dynamics (\Rightarrow spin current) \Rightarrow Electric current?

Yes. Exchange + Spin-orbit interactions

Spin Battery

Current pumping by magnetization dynamics

- ▶ Rashba spin-orbit α
- ▶ Exchange coupling J_{ex} to magnetization $M(x, t)$
- ▶ Naive result:



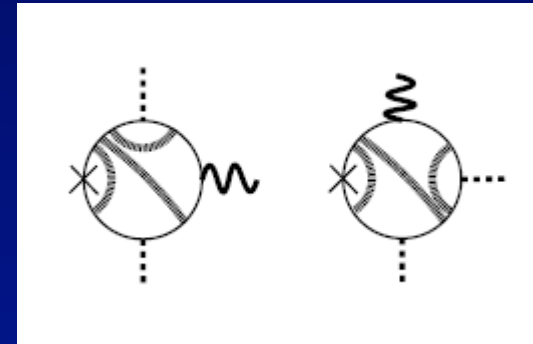
$$j_{\mu} \sim \text{tr}[k_{\mu} \alpha (k \times \sigma)_z J_{\text{ex}} (M \cdot \sigma)] \propto \alpha J_{\text{ex}} \epsilon_{\mu\nu z} k^2 M^{\nu}$$

- Saitoh Miyajima et al '06 experiment
- Stern '92, Barnes Maekawa '07, Duine '07
Voltage from spin Berry phase (fictitious flux)
- Ohe, Takeuchi & GT '07 perturbative

Electric current

Ohe, Takeuchi, GT

- Rashba spin-orbit α
- Exchange J



$$j_{\mu}^{(\text{ISH})}(x, t) = -\frac{4}{\pi} e m \alpha J_{\text{ex}}^2 \tau^2 \epsilon_{\mu\eta z} \int \frac{d^2 x_1}{a^2} D(x - x_1) (\mathbf{S}_x \times \dot{\mathbf{S}}_{x_1})_{\eta}$$

$$j_{\mu}^{\phi}(x, t) = \frac{4}{\pi^2} e \alpha J_{\text{ex}}^2 \tau^3 \frac{\partial}{\partial x_{\mu}} \epsilon_{\nu\eta z} \int \frac{d^2 x_1}{a^2} \int \frac{d^2 x_2}{a^2} D(x - x_1) \frac{\partial}{\partial x_{1\nu}} D^{(2)}(x_1 - x_2) (\mathbf{S}_{x_1} \times \dot{\mathbf{S}}_{x_2})_{\eta}$$

$$j_{\mu}^{(\text{ISH})} \sim -j_0 \epsilon_{\mu\eta z} \left\langle \mathbf{S} \times \dot{\mathbf{S}} \right\rangle_{\eta},$$

$$D(q) \propto 1/(Dq^2)$$

$$j_0 \propto \alpha J^2$$

$$j_{\mu}^{(\text{ISH})} = \gamma_{\text{ISH}} \epsilon_{\mu\nu z} (\nabla \cdot j_s^{(2)\nu}),$$

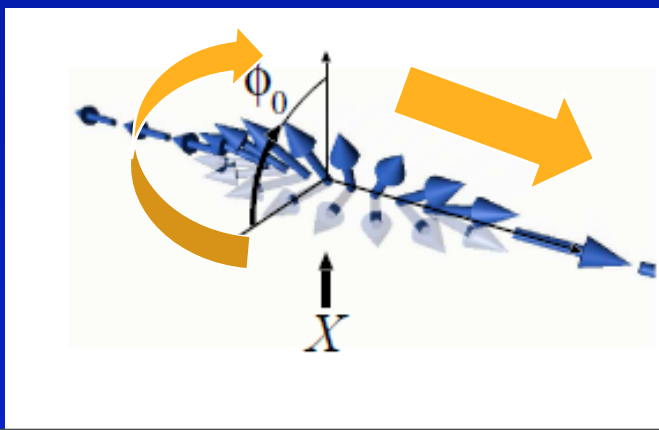
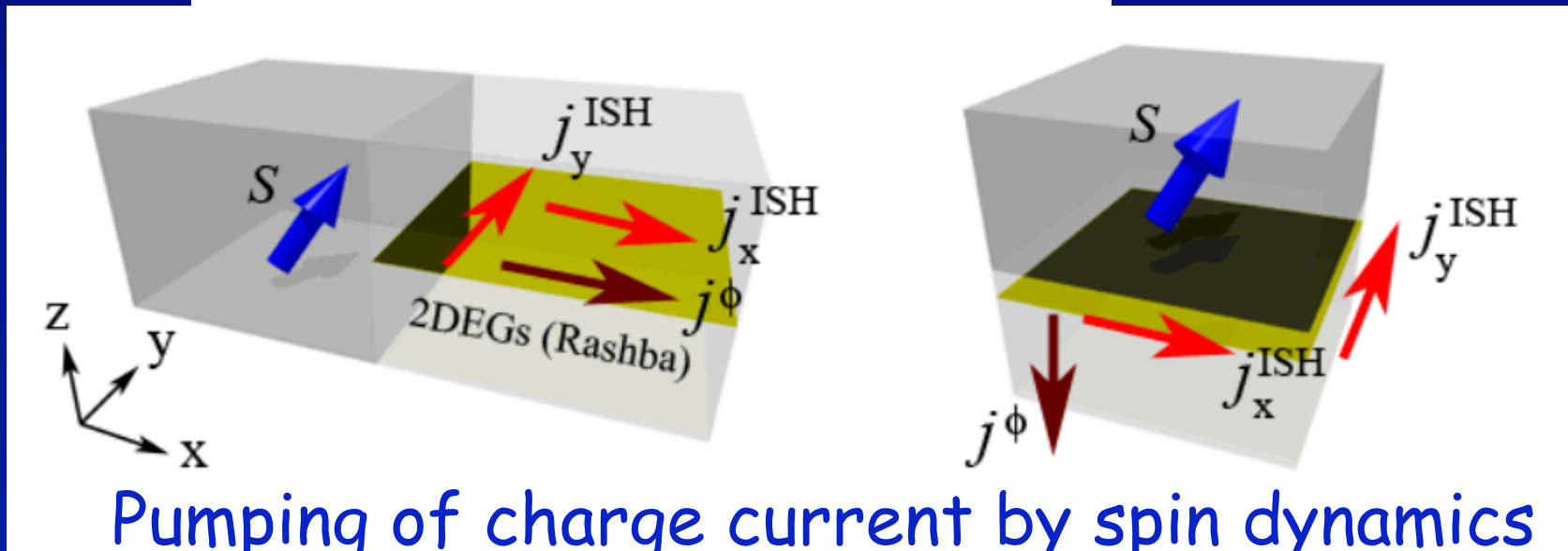
- Spin damping (spin current) \Rightarrow charge current

Conversion of magnetic energy into electric one

Pumped current Ohe, Takeuchi, GT

$$j_{\mu}^{(\text{ISH})} \sim -j_0 \epsilon_{\mu\eta z} \left\langle \mathbf{S} \times \dot{\mathbf{S}} \right\rangle_{\eta},$$

$$j_0 \propto \alpha J^2$$



$$j \propto \alpha J^2 \dot{X}, \alpha J^2 \dot{\phi}$$

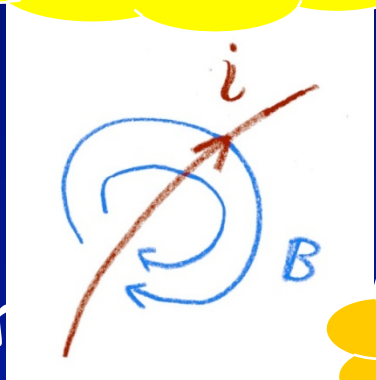
19 cent.

20 cent.~

21 cent.~(??)

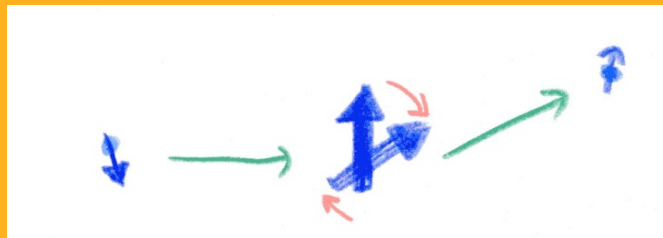
Maxwell equation

current
↓
magnetism



Ampere

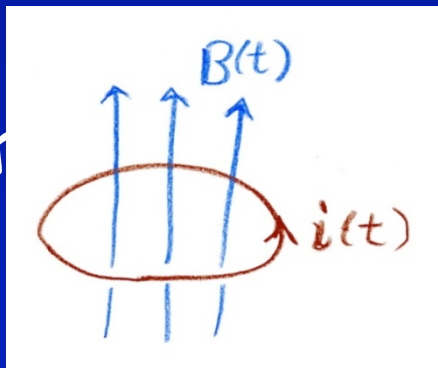
Material
and structure
Spin-orbit
Exchange interaction



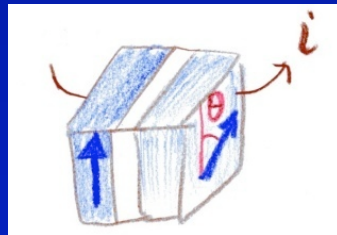
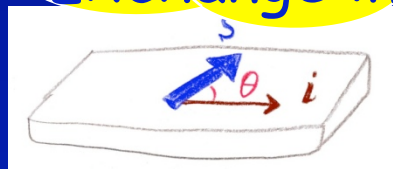
Spin transfer
Berger, Slonczewski
1978-, '96

Efficient in
Nano scale

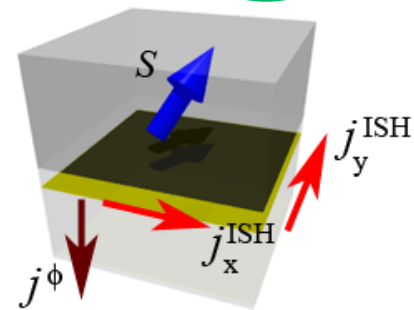
magnetism
↓
current



Faraday

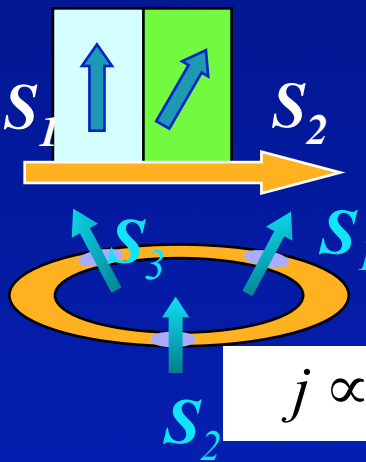


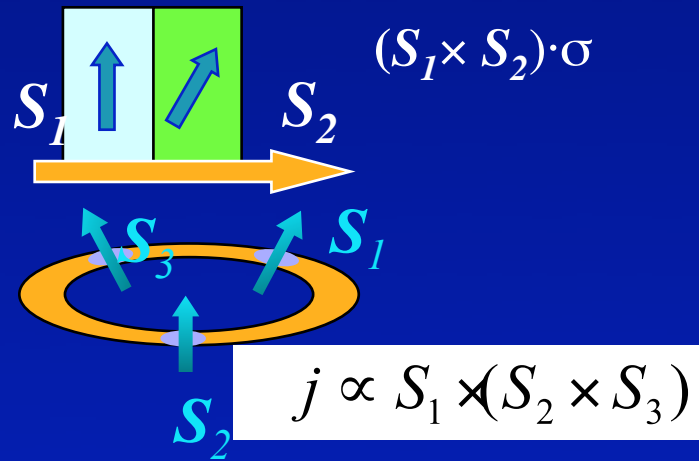
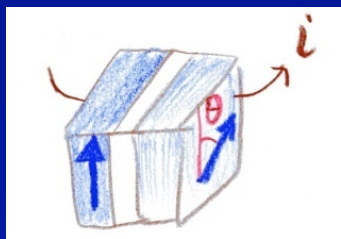
AMR, GMR('88),
TMR



Inverse spin Hall
Saitoh, Miyajima'06

スピン依存伝導：相互作用で分類

	輸送現象	電流による	磁化から
交換相互作用	デバイス GMR, TMR	磁化運動 スピン移行 トルク	電流生成 スピン流、電流
スピン軌道相互作用	AM 異常ホール スピンホール	直交した トルク 別の運動 モード	$(S_1 \times S_2) \cdot \sigma$  $j \propto S_1 \times (S_2 \times S_3)$ ダイレクトな電流 $j_{\mu}^{(ISH)} \sim -j_0 \epsilon_{\mu\eta z} \langle S \times \dot{S} \rangle_{\eta}$ スピン電池



$$j \propto S_1 \times (S_2 \times S_3)$$

$$j_{\mu}^{(ISH)} \sim -j_0 \epsilon_{\mu\eta z} \langle S \times \dot{S} \rangle_{\eta}$$

スピン電池

Local spin under current

Modified Landau-Lifshitz-Gilbert eq.

$$\begin{aligned} \dot{\vec{n}} = & \frac{g\mu_B}{\hbar} \vec{B}_{\text{eff}} \times \vec{n} + (\alpha_0 + \alpha_{\text{sf}}) \vec{n} \times \dot{\vec{n}} - \frac{s}{2S} \dot{\vec{n}} \\ & - \frac{a^3}{2e} (\vec{j}_s \cdot \nabla) \vec{n} - \beta_{\text{sf}} \frac{a^3}{e} [\vec{n} \times (\vec{j}_s \cdot \nabla) \vec{n}] \\ & + \vec{\tau}_{\text{nl}} \quad (O(\nabla^2 \vec{n})) \end{aligned}$$

(Spin-polarized) current \mathbf{j}

pushes and twists spin structure

Berger, Slonczewski, Zhang&Li, Thiaville et al....

Kohno GT Shibata

Summary

Current-driven domain wall dynamics

- For Low J_c and high wall speed
 $\sim 1/10$ ~ 10
- Origin of J_c
- Spin relaxation, non-adiabaticity
- Role of deformation on J_c

Pumping of charge current by spin dynamics

Spin-orbit interaction